



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Re: U.S. Patent Application 10,001,429 ) PATENT  
)  
German Title: Schreib-Leseverstärker für eine DRAM- )  
Speicherzelle sowie DRAM-Speicher )  
)  
English Translation: Read/write amplifier for a DRAM )  
Memory cell, and DRAM memory )  
)  
Applicant: Infineon Technologies, AG )  
)  
Inventors: Alexander Frey )  
)  
Attorney Docket No: 32226.14 )

RECEIVED

APR 15 2002

Honorable Commissioner of Patents and Trademarks  
Washington, D.C. 20231

Technology Center 2100

Sir:

**PRELIMINARY AMENDMENT**

In the above-entitled patent application, please amend the application as follows:

In the Claims

- 1 1. (amended) A read/write amplifier for a DRAM memory cell, which, for
- 2 evaluation of the information content of at least one DRAM memory cell, is connected or can be
- 3 connected to at least one bit line and to at least one reference bit line, which in each case form a
- 4 bit line pair, having a number of components for assessment, amplification and forwarding of
- 5 voltage signals read from the bit lines and reference bit lines, in which case the read/write
- 6 amplifier has a first read/write amplifier element and a second read/write amplifier element
- 7 separate therefrom, and in that the individual amplifier components are divided between the two
- 8 read/write amplifier elements.